



DATE: April 17, 2026

PCN #: 2797

PCN Title: Additional AT sites CAT, SAT, die revision and identification code marking change – Automotive

Dear Customer:

This is an announcement of change(s) to products that are currently being offered by Diodes Incorporated.

We request that you acknowledge receipt of this notification within 30 days of the date of notification by contacting your local Diodes sales representative. If you require samples for evaluation purposes, please submit a corresponding request within 30 days as well. Otherwise, samples may not be built prior to the implementation of the announced change(s).

The change(s) announced in this PCN will not be implemented prior to the target implementation date, i.e. 90 days from the stated notification date, unless Diodes receives written customer approval before that date.

Previously agreed upon customer specific product and/or process change requirements will be addressed separately.

For questions or clarification regarding this PCN, please contact your local Diodes sales representative.

Sincerely,

Diodes Incorporated PCN Team



PRODUCT CHANGE NOTICE

PCN-2797-REV1

Notification Date:	Implementation Date:	Product Family:	Change Type:	PCN #:
April 17, 2026	July 16, 2026	Analog	Additional AT sites, die revision, marking change	2797
TITLE				
Additional AT sites CAT, SAT, die revision and identification code marking change				
DESCRIPTION OF CHANGE				
This PCN is being issued to notify customers that in order to assure continuity of supply, Diodes has qualified additional manufacturing sites and Bill of Material (BOM) changes: • Diodes internal AT site (SAT) in Shanghai, China. • Diodes internal AT site (CAT) in Chengdu, China. • Diodes internal CP site (CAT) in Chengdu, China. Full electrical characterization and high reliability testing has been completed on representative part numbers to ensure there is no change to device functionality or electrical specifications in the datasheet. There will be no change to Form, Fit or Function of products unless specified in Table 5A – Change in identification code affecting top marking.				
IMPACT				
Continuity of Supply. No change in datasheet electrical parameters and product performance.				
PRODUCTS AFFECTED				
• Table 1 - Additional die revision (metal only) • Table 2 - Additional AT site (SAT) • Table 3 -Additional AT site (CAT) • Table 4 - Additional CP site (CAT) • Table 5 - Additional AT site (CAT) with Identification code marking change in both (CAT) and (SAT) See Table 5A				
WEB LINKS				
Manufacturer’s Notice:	https://www.diodes.com/quality/product-change-notices/diodes-product-change-notices/			
For More Information Contact:	https://www.diodes.com/about/contact-us/contact-sales/			
Data Sheet:	https://www.diodes.com/catalog/			
DISCLAIMER				
Unless a Diodes Incorporated Sales representative is contacted in writing within 30 days from the notification date of this PCN, all changes described in this announcement are considered approved.				

Table 1 - Additional die revision (metal only)

AL5816QW5-7					
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Table 2 - Additional AT site (SAT)

ZXCT1008QFTA	ZXCT1008QFTC	ZXCT1009QFTA			
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Table 3 -Additional AT site (CAT)

LM4040B33QFTA	LM4040B41QFTA	LM4040C33QFTA	LM4040C41QFTA	LM4040D33QFTA	LM4040D41QFTA
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Table 4 - Additional CP site (CAT)

AP64100QSP-13	AP64102QSP-13	AP64200QSP-13	AP64202QSP-13	AP64350QSP-13	AP64351QSP-13
AP64352QSP-13	AP64500QSP-13	AP64501QSP-13	AP64502QSP-13		

Table 5 - Additional AT site (CAT) with Identification code marking change in both (CAT) and (SAT) See Table 5A

LM4040B25QFTA	LM4040B30QFTA	LM4040B50QFTA	LM4040C25QFTA	LM4040C30QFTA	LM4040C50QFTA
LM4040D25QFTA	LM4040D30QFTA	LM4040D50QFTA	LM4041CQFTA	LM4041DADJQFTA	LM4041DQFTA

Table: 5A

Part Number	Current Identification Code	New Identification Code
LM4040B25QFTA	R2B	2B5Q
LM4040B30QFTA	R3B	3B0Q
LM4040B50QFTA	R5B	5B0Q
LM4040C25QFTA	R2C	2C5Q
LM4040C30QFTA	R3C	3C0Q
LM4040C50QFTA	R5C	5C0Q
LM4040D25QFTA	R2D	2D5Q
LM4040D30QFTA	R3D	3D0Q
LM4040D50QFTA	R5D	5D0Q
LM4041CQFTA	R1C	R1CQ
LM4041DQFTA	R1D	R1DQ
LM4041DADJQFTA	RAD	RADQ



Certificate of Design, Construction & Qualification

Description : Qualification of ZXCT1008QFTA&ZXCT1009QFTA to AEC Grade 1

General			Part Number			Die Revision			Package			Wire Bond, Cu Piller, Bump, CSP			MSL Level			Die Quantity (eg. Die per package)			Die Name(1)			Die Size (W/L/Thickness			Die Process / Technology			No of masks Steps			Wire Bond Material (Au, Cu, Al)			Wire Diameter			Wafer FAB			Wafer Diameter			Wafer Thickness			Top Metal Type/Bond Pad Composition			Top Metal Thickness			Die passivation thickness range			No of masks Steps			Saw Operation Site			Saw Step			BackgrindThickness			Backgrind Location			Bond Type (at Die)			Bond Type (at LF)			DB Epoxy/Solder Type			Die Attach Material			Leadframe Type			Leadframe Material (Stamped or Etched)			Ag plated or Bare Cu			Molding Compound Type			Assembly Site			FT Test Site			Realibility Test Site			Qual Plan #		
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General			Part Number			Die Revision			Package			Wire Bond, Cu Piller, Bump, CSP			MSL Level			Die Quantity (eg. Die per package)			Die Name(1)			Die Size (W/L/Thickness			Die Process / Technology			No of masks Steps			Wire Bond Material (Au, Cu, Al)			Wire Diameter			Wafer FAB			Wafer Diameter			Wafer Thickness			Top Metal Type/Bond Pad Composition			Top Metal Thickness			Die passivation thickness range			No of masks Steps			Saw Operation Site			Saw Step			BackgrindThickness			Backgrind Location			Bond Type (at Die)			Bond Type (at LF)			DB Epoxy/Solder Type			Die Attach Material			Leadframe Type			Leadframe Material (Stamped or Etched)			Ag plated or Bare Cu			Molding Compound Type			Assembly Site			FT Test Site			Realibility Test Site			Qual Plan #		
General			Part Number			Die Revision			Package			Wire Bond, Cu Piller, Bump, CSP			MSL Level			Die Quantity (eg. Die per package)			Die Name(1)			Die Size (W/L/Thickness			Die Process / Technology			No of masks Steps			Wire Bond Material (Au, Cu, Al)			Wire Diameter			Wafer FAB			Wafer Diameter			Wafer Thickness			Top Metal Type/Bond Pad Composition			Top Metal Thickness			Die passivation thickness range			No of masks Steps			Saw Operation Site			Saw Step			BackgrindThickness			Backgrind Location			Bond Type (at Die)			Bond Type (at LF)			DB Epoxy/Solder Type			Die Attach Material			Leadframe Type			Leadframe Material (Stamped or Etched)			Ag plated or Bare Cu			Molding Compound Type			Assembly Site			FT Test Site			Realibility Test Site			Qual Plan #		
General			Part Number			Die Revision			Package			Wire Bond, Cu Piller, Bump, CSP			MSL Level			Die Quantity (eg. Die per package)			Die Name(1)			Die Size (W/L/Thickness			Die Process / Technology			No of masks Steps			Wire Bond Material (Au, Cu, Al)			Wire Diameter			Wafer FAB			Wafer Diameter			Wafer Thickness			Top Metal Type/Bond Pad Composition			Top Metal Thickness			Die passivation thickness range			No of masks Steps			Saw Operation Site			Saw Step			BackgrindThickness			Backgrind Location			Bond Type (at Die)			Bond Type (at LF)			DB Epoxy/Solder Type			Die Attach Material			Leadframe Type			Leadframe Material (Stamped or Etched)			Ag plated or Bare Cu			Molding Compound														



			Do not removed these columns				Qual Device1 - Lot 1		Qual Device1 - Lot 2		Qual Device1 - Lot3					
General	Part Number						LM4040B25QFTA		LM4040B25QFTA		LM4040B25QFTA					
	Package						SSOT-23		SSOT-23		SSOT-23					
	Wire Bond, Cu Pillar, Bump, CSP						Wire Bond		Wire Bond		Wire Bond					
	MSL Level						MSL1		MSL1		MSL1					
	Die Quantity (eg. Die per package)						1		1		1					
	Die Name(1)						LM404025QN		LM404025QN		LM404025QN					
	Die Size (W/L/Thickness						0.680*0.680*0.205mm		0.680*0.680*0.205mm		0.680*0.680*0.205mm					
	Die Process / Technology						ZAD 20V Bipolar		ZAD 20V Bipolar		ZAD 20V Bipolar					
	No of masks Steps						13		13		13					
	Wire Bond Material (Au, Cu, Al)						Cu		Cu		Cu					
	Wire Diameter						0.8mil		0.8mil		0.8mil					
Fab	Wafer FAB						OFAB		OFAB		OFAB					
	Wafer FAB Location						UK		UK		UK					
	Wafer Diameter						6 inch		6 inch		6 inch					
	Wafer Thickness						675um		675um		675um					
	Top Metal Type/Bond Pad Composition						AlCu0.5		AlCu0.5		AlCu0.5					
	Top Metal Thickness						2um		2um		2um					
	Die passivation thickness range						5000Å(+/-500Å)SiO2 + 5000Å(+/-500Å)SiN		5000Å(+/-500Å)SiO2 + 5000Å(+/-500Å)SiN		5000Å(+/-500Å)SiO2 + 5000Å(+/-500Å)SiN					
	No. of bond over active area						2		2		2					
	Glass Transition Temp						125° C		125°C		125°C					
	Header plating (Die Land Area)						Ag 3.0-8.0um		Ag 3.0-8.0um		Ag 3.0-8.0um					
	Max Junction Temp						150° C		150°C		150°C					
	Max Thermal resistance Junc (ambient)						380° C/W		380°C/W		380°C/W					
	No of masks Steps						13		13		13					
Saw	Saw Operation Site						CAT		CAT		CAT					
	Saw Step						2		2		2					
Package	BackgrindThickness						205+/-10		205+/-10		205+/-10					
	Backgrind Location						CAT		CAT		CAT					
	Bond Type (at Die)						Ball		Ball		Ball					
	Bond Type (at LF)						Wedge		Wedge		Wedge					
	DB Epoxy/Solder Type						EPOXY		EPOXY		EPOXY					
	Die Attach Material						84-1LMISR4-TF		84-1LMISR4-TF		84-1LMISR4-TF					
	Leadframe Type						SOT-23T (Etching)		SOT-23T (Etching)		SOT-23T (Etching)					
	Leadframe Material						A194		A194		A194					
	Ag plated or Bare Cu						Copper plating		Copper plating		Copper plating					
	Molding Compound Type						CEL-1700HF40SK-D3 (M2)		CEL-1700HF40SK-D3 (M2)		CEL-1700HF40SK-D3 (M2)					
AT/Rel	Assembly Site						CAT		CAT		CAT					
	FT Test Site						CAT		CAT		CAT					
	Realibility Test Site						CAT		CAT		CAT					
	Qual Plan #						24082701		24082701		24082701					
Test	Test Conditions	Duration / Limits					Test Method	Test Group	Fail/SS	Lots Required	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail
MSL1 Pre-cond	(JESD22-A113) Bake 125C	24 Hrs					JESD22 A113 JEDC J-STD-020	A	0/154	3 Assy lots	X	Pass	X	Pass	X	Pass
	Soak 85C, 85% RH	168Hrs						A	0/154	3 Assy lots	X	Pass	X	Pass	X	Pass
	IR reflow 260C	3 cycles						A	0/154	3 Assy lots	X	Pass	X	Pass	X	Pass
Temp Cycle (TC)	(JESD22-A104) -65C-150C Mounted on PCB Board	500 cycles					JEDD22 A104 AEC-Q006	A	0/77	3 Assy lots	X	Pass	X	Pass	X	Pass
		1000 cycles						A	0/77	3 Assy lots	X	Pass	X	Pass	X	Pass
HAST	JESD22-A101/A110 130C, 85%RH 33.3 psia Vcc = Op Max	96 Hrs					JESD22-A110	A	0/77	3 Assy lots	X	Pass	X	Pass	X	Pass
UHAST	JESD22-A118 130C, 85%RH 33.3 psia	96 Hrs					JEDD22 A118	A	0/77	3 Assy lots	X	Pass	X	Pass	X	Pass
HTSL High Temperature Storage	(JESD22-A103) Ta>150C	168 Hrs					JESD A103	A	0/77	3 Assy lots	X	Pass	X	Pass	X	Pass
		500 Hrs						A	0/77	3 Assy lots	X	Pass	X	Pass	X	Pass
		1000 Hrs		A	0/77	3 Assy lots	X	Pass	X	Pass	X	Pass				
WBS	JESD22-B116B	Cpk>1.66	AEC-Q100-001	C	0/5	30 Bonds	X	Pass	X	Pass	X	Pass				
WBP	MIL-STD883-2011	Cpk>1.66	MIL-STD883-2011	C	0/5	30 Bonds	X	Pass	X	Pass	X	Pass				
Crater	Crater Testing (Min 30 Bonds from 5 Devices)	TBD		C	0/30 Bonds	3 Assy	X	Pass	X	Pass	X	Pass				
SD Solderability	>															



			Do not remove these columns			Qual Device 1		QBS parts list		QBS Source Device 1		QBS Source Device 2		QBS Source Device 3																
General	Part Number					LM4040C41QFTA	LM4040B25FTA LM4040B33QFTA LM4040B41FTA LM4040B50FTA LM4040C25FTA LM4040C30QFTA LM4040C33QFTA LM4040C41FTA LM4040C50FTA LM4040D25FTA LM4040D25FTA-73 LM4040D30FTA LM4040D33QFTA LM4040D41FTA LM4040D50FTA LM4041CFTA LM4041DFTA LM4041DADJFTA LM4040B33QQFTA LM4040B41QFTA LM4040C33QQFTA LM4040C41QFTA LM4040C50QFTA LM4040D33QQFTA LM4040D41QFTA LM4041CQFTA LM4041DQFTA																							
																Package			SSOT-23			SSOT-23			SSOT-23			SSOT-23		
																Wire Bond, Cu Piller, Bump, CSP			Wire Bond			Wire Bond			Wire Bond			Wire Bond		
																MSL Level			MSL1			MSL1			MSL1			MSL1		
																Die Name(1)			LM404041N			Refer to CDC file			LM404025QN			LM404025QN		
																Die Size (W/L/Thickness			0.680*0.680*0.205mm			0.680*0.680*0.205mm			0.680*0.680*0.205mm			0.680*0.680*0.205mm		
																Die Process / Technology			ZAD 20V Bipolar			ZAD 20V Bipolar			ZAD 20V Bipolar			ZAD 20V Bipolar		
																Wire Bond Material (Au, Cu, Al)			Cu			Cu			Cu			Cu		
																Wire Diameter			1.0mil			1.0mil			0.8mil			0.8mil		
																Fab	Wafer FAB		OFAB			OFAB			OFAB			OFAB		
																Wafer FAB Location			UK			UK			UK			UK		
																Wafer Diameter			6 inch			6 inch			6 inch			6 inch		
																Wafer Thickness			675um			675um			675um			675um		
																Top Metal Type/Bond Pad Composition			AlCu0.5			AlCu0.5			AlCu0.5			AlCu0.5		
																Top Metal Thickness			2.6um			2.6um			2um			2um		
																Die passivation thickness range			5000Å(+/-500Å)/SiO2 + 5000Å(+/-500Å)/SiN			5000Å(+/-500Å)/SiO2 + 5000Å(+/-500Å)/SiN			5000Å(+/-500Å)/SiO2 + 5000Å(+/-500Å)/SiN			5000Å(+/-500Å)/SiO2 + 5000Å(+/-500Å)/SiN		
																Glass Transistion Temp			125° C			125° C			125° C			125° C		
																Max Junction Temp			150° C			150° C			150° C			150° C		
																Max Thermal resistance Junc (ambient)			380° C/W			380° C/W			380° C/W			380° C/W		
																Bond Type (at Die)			Ball			Ball			Ball			Ball		
																Bond Type (at LF)			Stitch			Stitch			Stitch			Stitch		
																DB Epoxy/Solder Type			EPOXY			EPOXY			EPOXY			EPOXY		
																Die Attach Material			84-1LMISR4-TF			84-1LMISR4-TF			84-1LMISR4-TF			84-1LMISR4-TF		
																Leadframe Type			SOT-23T (Etching)			SOT-23T (Etching)			SOT-23T (Etching)			SOT-23T (Etching)		
Molding Compound Type			CEL-1700HF40SK-D3 (M2)			CEL-1700HF40SK-D3 (M2)			CEL-1700HF40SK-D3 (M2)			CEL-1700HF40SK-D3 (M2)																		
Molding Compound Manufacturer			SD			SD			SD			SD																		
AT/Rel	Assembly Site		CAT			CAT			CAT			CAT																		
	FT Test Site		CAT			CAT			CAT			CAT																		
	Reliability Test Site		CAT			CAT			CAT			CAT																		
	Qual Plan #		25091601			25091601			24082701			24082701																		
Test	Test Conditions	Duration / Limits	Test Method	Fail/SS	Lots Required	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail															
MSL1 Pre-cond	(JESD22-A113) Bake 125C	24 Hrs	JESD22 A113 JEDC J-STD-020	0/154	3 Assy lots	QBS for QBS Source Device 1,2,3	Pass	QBS for QBS Source Device 1,2,3	Pass	X	Pass	X	Pass	X	Pass															
	Soak 85C, 85% RH	168Hrs		0/154	3 Assy lots	QBS for QBS Source Device 1,2,3	Pass	QBS for QBS Source Device 1,2,3	Pass	X	Pass	X	Pass	X	Pass															
	IR reflow 260C	3 cycles		0/154	3 Assy lots	QBS for QBS Source Device 1,2,3	Pass	QBS for QBS Source Device 1,2,3	Pass	X	Pass	X	Pass	X	Pass															
Temp Cycle (TC) Option 1 (AEC-Q006)	(JESD22-A104) -65C-150C Mounted on PCB Board	500 cycles	JEDD22 A104	0/77	3 Assy lots	QBS for QBS Source Device 1,2,3	Pass	QBS for QBS Source Device 1,2,3	Pass	X	Pass	X	Pass	X	Pass															
		1000 cycles		0/77	3 Assy lots	QBS for QBS Source Device 1,2,3	Pass	QBS for QBS Source Device 1,2,3	Pass	X	Pass	X	Pass</																	

Certificate of Design, Construction & Qualification



Description: AL5816QW5-7_AL5816W5-7(SOT25) Standard Qual Plan

General			Do not remove these columns		Qual Device 1	Qual Device 2	QBS Source Device 1	QBS Source Device 2	QBS Source Device 3	QBS Source Device 4	QBS Source Device 5	QBS Source Device 6
	Part Number		AL5816QW5-7	AL5816QW5-7	AL5816QW5-7	AL5816QW5-7	AL5816QW5-7	AL5816QW5-7	AL5816QW5-7	AL5816QW5-7	AL5816QW5-7	AL5816QW5-7
	Die Revision		AD08070423C0	AD08070423C0	AD08070423B0	AD08070423B0	AD08070423B0	AD08070423B0	AD08070423B0	AD08070423B0	AD08070423B0	AD08070423B0
	Package		SOT25	SOT25	SOT25	SOT25	SOT25	SOT25	SOT25	SOT25	SOT25	SOT25
	Wire Bond, Cu Piller, Bump, CSP		Wire Bond	Wire Bond	Wire Bond	Wire Bond	Wire Bond	Wire Bond	Wire Bond	Wire Bond	Wire Bond	Wire Bond
	MSL Level		MSL1	MSL1	MSL1	MSL1	MSL1	MSL1	MSL1	MSL1	MSL1	MSL1
Die Name(1)			AD08070423C0	AD08070423C0	AD08070423B0	AD08070423B0	AD08070423B0	AD08070423B0	AD08070423B0	AD08070423B0	AD08070423B0	AD08070423B0
	Die Size (W/L/Thickness		1000*1200* 205(um)	1000*1200* 205(um)	1000*1200* 205(um)	1000*1200* 205(um)	1000*1200* 205(um)	1000*1200* 205(um)	1000*1200* 205(um)	1000*1200* 205(um)	1000*1200* 205(um)	1000*1200* 205(um)
	Die Process / Technology		BCD 0.18um 1P3M 5.0V/60V	BCD 0.18um 1P3M 5.0V/60V	BCD 0.18um 1P3M 5.0V/60V	BCD 0.18um 1P3M 5.0V/60V	BCD 0.18um 1P3M 5.0V/60V	BCD 0.18um 1P3M 5.0V/60V	BCD 0.18um 1P3M 5.0V/60V	BCD 0.18um 1P3M 5.0V/60V	BCD 0.18um 1P3M 5.0V/60V	BCD 0.18um 1P3M 5.0V/60V
	Wire Bond Material (Au, Cu, Al)		Au	PdCu	Au	PdCu	PdCu	PdCu	PdCu	PdCu	PdCu	PdCu
	Wire Diameter		0.8 mil	0.8 mil	0.8 mil	0.8 mil	0.8 mil	0.8 mil	0.8 mil	0.8 mil	0.8 mil	0.8 mil
	Wafer FAB		DongBu Korea	DongBu Korea	DongBu Korea	DongBu Korea	DongBu Korea	DongBu Korea	DongBu Korea	DongBu Korea	DongBu Korea	DongBu Korea
	Wafer FAB Location		Korea	Korea	Korea	Korea	Korea	Korea	Korea	Korea	Korea	Korea
	Wafer Diameter		8"	8"	8"	8"	8"	8"	8"	8"	8"	8"
	Wafer Thickness		725um	725um	725um	725um	725um	725um	725um	725um	725um	725um
	Top Metal Type/Bond Pad Composition		AlCu	AlCu	AlCu	AlCu	AlCu	AlCu	AlCu	AlCu	AlCu	AlCu
Fab	Top Metal Thickness		2.7um	2.7um	2.7um	2.7um	2.7um	2.7um	2.7um	2.7um	2.7um	2.7um
	Die passivation thickness range		SIN 6000A+Oxide 11000A	SIN 6000A+Oxide 11000A	SIN 6000A+Oxide 11000A	SIN 6000A+Oxide 11000A	SIN 6000A+Oxide 11000A	SIN 6000A+Oxide 11000A	SIN 6000A+Oxide 11000A	SIN 6000A+Oxide 11000A	SIN 6000A+Oxide 11000A	SIN 6000A+Oxide 11000A
	Glass Transition Temp		130 degree C	130 degree C	130 degree C	130 degree C	130 degree C	130 degree C	130 degree C	130 degree C	130 degree C	130 degree C
	Max Junction Temp		150 degree C	150 degree C	150 degree C	150 degree C	150 degree C	150 degree C	150 degree C	150 degree C	150 degree C	150 degree C
	Metal Layers		3	3	3	3	3	3	3	3	3	3
	BackgrindThickness		205um	205um	205um	205um	205um	205um	205um	205um	205um	205um
	Backgrind Location		SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT
	Bond Type (at Die)		Ball	Ball	Ball	Ball	Ball	Ball	Ball	Ball	Ball	Ball
	Bond Type (at LF)		Wedge	Wedge	Wedge	Wedge	Wedge	Wedge	Wedge	Wedge	Wedge	Wedge
	DB Epoxy/Solder Type		Epoxy	Epoxy	Epoxy	Epoxy	Epoxy	Epoxy	Epoxy	Epoxy	Epoxy	Epoxy
Package	Die Attach Material		84-1LMISR4	839C-HT	84-1LMISR4	84-1LMISR4	84-1LMISR4	84-1LMISR4	84-1LMISR4/R309C-HT	84-1LMISR4/R309C-HT	84-1LMISR4/R309C-HT	84-1LMISR4/R309C-HT
	Leadframe Type		SOT-25J	SOT-25J	SOT-25J	SOT-25J	SOT-25J	SOT-25J	SOT-25J	SOT-25J	SOT-25J	SOT-25J
	Molding Compound Type		CEL-1700HF40SK-D3	CEL-1700HF40SK-D3	CEL-1700HF40SK-D3	CEL-1700HF40SK-D3	CEL-1700HF40SK-D3	CEL-1700HF40SK-D3	CEL-1700HF40SK-D3	CEL-1700HF40SK-D3	CEL-1700HF40SK-D3	CEL-1700HF40SK-D3
	Molding Compound Manufacturer		Resonac Materials (Suzhou)	Resonac Materials (Suzhou)	Resonac Materials (Suzhou)	Resonac Materials (Suzhou)	Resonac Materials (Suzhou)	Resonac Materials (Suzhou)	Resonac Materials (Suzhou)	Resonac Materials (Suzhou)	Resonac Materials (Suzhou)	Resonac Materials (Suzhou)
	Green Compound (Yes/No)		Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
	Lead-Free (Yes/No)		Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
	Assembly Site		SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT
	FT Test Site		SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT
	Realibility Test Site		SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT	SAT
	Qual Plan #		#25103001	#25103001	#18051703	#18051703	#18051703	#18051703	#17030201/#24112202	#17030201/#24112202	#17030201/#24112202	#17030201/#24112202

Test Group	Test	Test Conditions	Duration / Limits	Test Method	Fail/SS	Lots Required	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail			X = Test Needed	Results Pass/Fail
	Test Group A - Accelerated Environment Stress Tests																					
A1	MSL1 Pre-cond	(JESD22-A113) Bake 125C	24 Hrs	JESD22 A113 JEDC J-STD-Q20	0/154	3 Assy lots	QBS to QBS Device1~3		QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4	
A1		Soak 85C, 85% RH	168Hrs		0/154	3 Assy lots	QBS to QBS Device1~3		QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4	
A1		IR reflow 260C	3 cycles			0/154	3 Assy lots	QBS to QBS Device1~3		QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4
A4	Temp Cycle (TC) Post TC Wire Bond Pull and Stitch Post TC CSAM	(JESD22-A104) -65C-150C Mounted on PCB Board (Daughter Card)	500 cycles	JEDD22 A104	0/77	3 Assy lots	QBS to QBS Device1~3		QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4	
A4			1000 cycles		0/77	3 Assy lots	QBS to QBS Device1~3		QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4	
A4			Post TC (Max 30 Bonds per Device) Note (3)	post 1000 cyc	MIL-STD883-2011	0/30 Bonds	3 Assy lots		QBS to QBS Device 4~6							X	Pass				QBS to QBS Device 4	
A4			CSAM post 1000 cyc TC (If performing 2X then 1X CSAM may be waived if mounted on PCB board)	post 1000 cyc		Marked 11	3 Assy lots		QBS to QBS Device 4~6							X	Pass				QBS to QBS Device 4	
A2	HA ST	JESD22-A101/A110 130C, 85%RH 33.3 psia Vcc = Op Max or up to a voltage above which arcing in the chamber will likely occur (typically 42V); PER JESD22-A110	96 Hrs	JESD22-A110	0/77	3 Assy lots	X	PASS	QBS to Qual Device1		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4	
A3		UHAST	JESD22-A118 130C, 85%RH 33.3 psia	96 Hrs	JEDD22 A118	0/77	3 Assy lots	QBS to QBS Device1~3		QBS to QBS Device1~3		X	Pass	X	Pass	X	Pass					
A6	HTSL High Temperature Storage	(JESD22-A103) Ta=175C for Grade 0 Ta>150C	168 Hrs	JESD A103	0/45	3 Assy lots	QBS to QBS Device1~3		QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4	
A6			500 Hrs		0/45	3 Assy lots	QBS to QBS Device1~3		QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4	
A6			1000 Hrs			0/45	3 Assy lots	QBS to QBS Device1~3		QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4
Test Group B - Accelerated Lifetime Simulation Tests																						
B1	HTOL	Ta=125C, 100% Vcc	168 Hrs	JESD22 A108	0/77	3 WF	X	PASS	QBS to Qual Device1		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4	
B1		or Ta=150 for 408 hrs	500 Hrs	JESD22 A108	0/77	3 WF	Additional	PASS	QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4	
B1			1000 Hrs	JESD22 A108	0/77	3 WF	Additional	PASS	QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	QBS to QBS Device 4	
B2	ELFR Earlier Life Failure Rate	Ta=125C, 100% Vcc	48 hrs	AEC-Q100-008	0/800	3 WF	QBS to QBS Device1~3				X	Pass	X	Pass	X	Pass						
Test Group C - Package Assembly Integrity Tests																						
C1	WBS	JESD22-B116B	Cpk<1.66	AEC-Q100-001	0/5	30 Bonds	Additional	PASS	Additional	PASS	X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	X	Pass
C2	WBP	MIL-STD883-2011	Cpk<1.66	MIL-STD883-2011	0/5	30 Bonds	Additional	PASS	Additional	PASS	X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	X	Pass
C3	SD Solderability	>95% Coverage	5 Seconds	JESD22 B102	0/15	1 Assy	QBS to QBS Device1~3		QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	X	Pass
C4	PD Physical Dimensions		Package Outline	JESD22 B100 JESD22 B108	0/3 with Cpk<1.67	3 Assy	QBS to QBS Device1~3		QBS to QBS Device 4~6		X	Pass	X	Pass	X	Pass	X	Pass	X	Pass	X	Pass
Test Group E - Electrical Verification																						
E2	HBM Human Body Model	HBM (AEC-Q100-002)	+2KV	(AEC-Q100-002)	0/3	1 WF	X	PASS	QBS to Qual Device1		X	PASS					X	PASS			X	PASS
E3	CDM Charged Device Model	CDM (AEC-Q100-011)	>750	(AEC-Q100-011)	0/3	1 WF	X	PASS	QBS to Qual Device1		X	PASS					X	PASS			X	PASS
E4	LU Latch-up (Class II)	Max Operating Ta or Tc or Tj	100mA	AEC Q100-004	0/6	1 WF	X	PASS	QBS to Qual Device1		X	PASS					X	PASS			X	PASS
E7	Char Characterization	Typ -40C, 0C, 25C, 85C, 125C	Operating Range	AEC-Q003	0/30		X	PASS	QBS to Qual Device1		X	PASS			X	PASS	X	PASS				
	Summary: Submitted By: Approved By:	Rick Chen 3/13/2026 Rick Chen 10/30/2025 Daniel Li 3/24/2026																				